AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

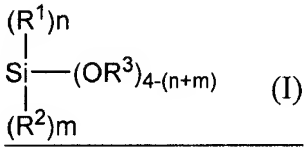
LISTING OF CLAIMS:

1 - 4. (canceled).

5. (currently amended): A method for forming ~~a silica-containing film~~an interlayer insulating film of a semiconductor element comprising the steps of applying a coating composition for forming ~~a silica-containing film as set forth in any one of the foregoing claims 1, 2 and 4~~an interlayer insulating film of a semiconductor element onto a base material and then drying the coated layer,

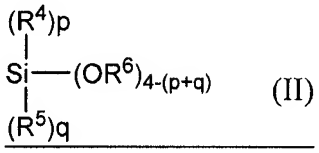
wherein said interlayer insulating film has a dielectric constant of not higher than 2.5, and

wherein said coating composition comprises (A) a hydrolyzate and/or partially condensed product of a compound represented by the following general formula (I) and a compound represented by the following general formula (II):



(I)

wherein R^1 represents a hydrogen atom, an alkyl group having 1 to 18 carbon atoms or an aryl group having 6 to 14 carbon atoms; R^2 represents an organic group having an unsaturated bond and 2 to 12 carbon atoms; R^3 represents an alkyl group having 1 to 6 carbon atoms; n is an integer ranging from 0 to 2; m is an integer ranging from 1 to 3, provided that n and m are selected such that they satisfy the following relation: $1 \leqq n + m \leqq 3$; and



(II)

wherein R^4 represents an alkyl group having 1 to 18 carbon atoms or an aryl group having 6 to 14 carbon atoms; R^5 represents a hydrogen atom; R^6 represents an alkyl group having 1 to 6 carbon atoms; and p and q are integers selected in such a manner that they satisfy the following relation: $0 \leqq p + q \leqq 3$;

(B) a solvent for coating; and

(C) at least one member selected from the group consisting of a void-forming solvent and hollow polymer fine particles.

6. (canceled).

7. (new): The method as set forth in claim 5, wherein the component (C) comprises a void-forming solvent.

8. (new): The method as set forth in claim 7, wherein the void-forming solvent is 1,2-diol or 1,n-diol having a boiling point of not less than 200°C.

9. (new): The method as set forth in claim 5, wherein the component (C) comprises hollow polymer fine particles.